

## 1200V N-Channel Silicon Carbide Power MOSFET

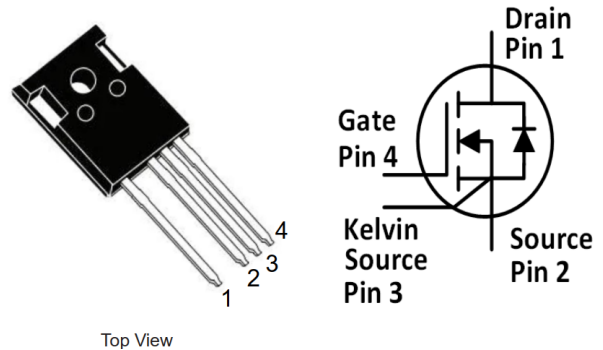
### Features:

- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- High operating junction temperature capability
- Very fast and robust intrinsic body diode

### Applications:

- Solar inverters
- UPS
- Motor drivers
- High voltage DC/DC converters
- Switch mode power supplies

### Package:



Part Number	Package
DTN40N120SC4	TO247-4

### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{DS}$	Drain-Source voltage	1200	V	$V_{GS}=0\text{V}$ , $I_D=100\mu\text{A}$	
$V_{GS}$	Gate-Source voltage	-5 to 20	V	Recommended maximum	
$I_D$	Drain current (continuous)	42	A	$V_{GS}=20\text{V}$ , $T_c=25^\circ\text{C}$	Fig. 21
		31	A	$V_{GS}=20\text{V}$ , $T_c=100^\circ\text{C}$	
$I_{DM}$	Drain current (pulsed)	70	A	Pulse width limited by SOA	Fig. 24
$P_{TOT}$	Total power dissipation	300	W	$T_c=25^\circ\text{C}$	Fig. 22
$T_{stg}$	Storage temperature range	-55 to 175	$^\circ\text{C}$		
$T_J$	Operating junction temperature	-55 to 175	$^\circ\text{C}$		
$T_L$	Solder Temperature	260	$^\circ\text{C}$	wave soldering only allowed at leads, 1.6mm from case for 10 s	

### Thermal Data

Symbol	Parameter	Value	Unit	Note
$R_{\theta(j-c)}$	Thermal Resistance from Junction to Case	0.5	$^\circ\text{C}/\text{W}$	Fig. 23

**Electrical Characteristics** ( $T_c=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
$I_{DSS}$	Zero gate voltage drain current		5	100	$\mu\text{A}$	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}$	
$I_{GSS}$	Gate leakage current			$\pm 100$	$\text{nA}$	$V_{DS}=0\text{V}, V_{GS}=-5\sim 20\text{V}$	
$V_{TH}$	Gate threshold voltage		3.6		$\text{V}$	$V_{GS}=V_{DS}, I_D=3.8\text{mA}$	Fig. 8, 9
			2.7			$V_{GS}=V_{DS}, I_D=3.8\text{mA}$ @ $T_c=175^\circ\text{C}$	
$R_{ON}$	Static drain-source on-resistance		80	100	$\text{m}\Omega$	$V_{GS}=20\text{V}, I_D=10\text{A}$ @ $T_j=25^\circ\text{C}$	Fig. 4, 5, 6, 7
			130		$\text{m}\Omega$	$V_{GS}=20\text{V}, I_D=10\text{A}$ @ $T_j=175^\circ\text{C}$	
$C_{iss}$	Input capacitance		1680		$\text{pF}$	$V_{DS}=800\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}, V_{AC}=25\text{mV}$	Fig. 16
$C_{oss}$	Output capacitance		69		$\text{pF}$		
$C_{rss}$	Reverse transfer capacitance		6.7		$\text{pF}$		
$E_{oss}$	$C_{oss}$ stored energy		27		$\mu\text{J}$		Fig. 17
$E_{AS}$	Avalanche energy, single pulse		0.75		$\text{J}$	$I_D=20\text{A}, V_{DD}=50\text{V},$ $L=2\text{mH}$	
$Q_g$	Total gate charge		76		$\text{nC}$	$V_{DS}=800\text{V}, I_D=20\text{A},$ $V_{GS}=-5\text{ to }20\text{V}$	Fig. 18
$Q_{gs}$	Gate-source charge		29		$\text{nC}$		
$Q_{gd}$	Gate-drain charge		34		$\text{nC}$		
$R_g$	Gate input resistance		4.2		$\Omega$	$f=1\text{MHz}$	
$E_{ON}$	Turn-on switching energy		154		$\mu\text{J}$	$V_{DS}=800\text{V}, I_D=20\text{A},$ $V_{GS}=-3.5\text{ to }20\text{V},$ $R_{G(\text{ext})}=2.0\Omega,$ $L=290\mu\text{H}$	Fig. 19, 20
$E_{OFF}$	Turn-off switching energy		80		$\mu\text{J}$		
$t_{d(\text{on})}$	Turn-on delay time		8.9		ns		
$t_r$	Rise time		19.9				
$t_{d(\text{off})}$	Turn-off delay time		14.7				
$t_f$	Fall time		9.5				

**Reverse Diode Characteristics** ( $T_c=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
$V_{SD}$	Diode forward voltage		4.7		V	$I_{SD}=10\text{A}, V_{GS}=0\text{V}$	Fig. 10, 11, 12
			4.2		V	$I_{SD}=10\text{A}, V_{GS}=0\text{V},$ $T_J=175^\circ\text{C}$	
$t_{rr}$	Reverse recovery time		10.2		ns	$V_{GS}=0\text{V}, I_{SD}=20\text{A},$	
$Q_{rr}$	Reverse recovery charge		64		nC	$V_R=800\text{V},$	
$I_{RRM}$	Peak reverse recovery current		11.3		A	$di/dt=1100\text{A}/\mu\text{s}$	

Typical Performance (curves)

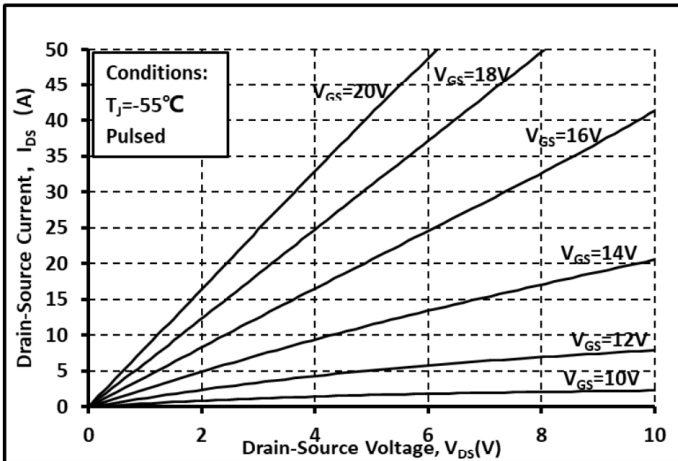


Fig. 1 Output Curve @  $T_j = -55^\circ\text{C}$

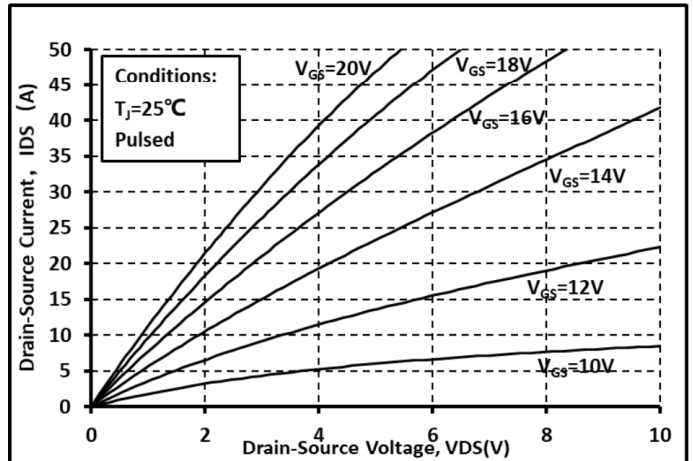


Fig. 2 Output Curve @  $T_j = 25^\circ\text{C}$

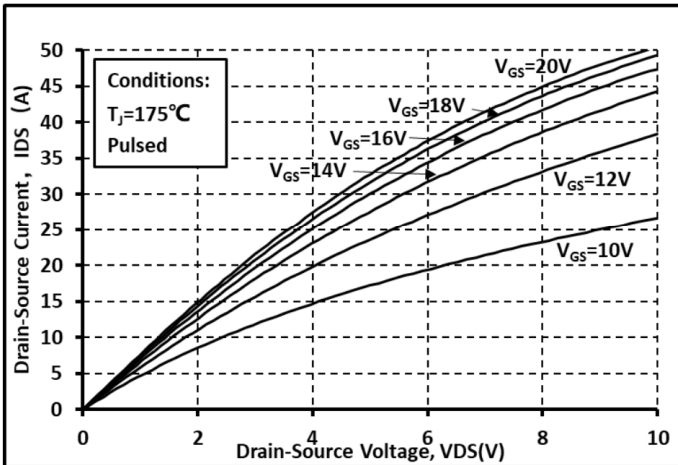


Fig. 3 Output Curve @  $T_j = 175^\circ\text{C}$

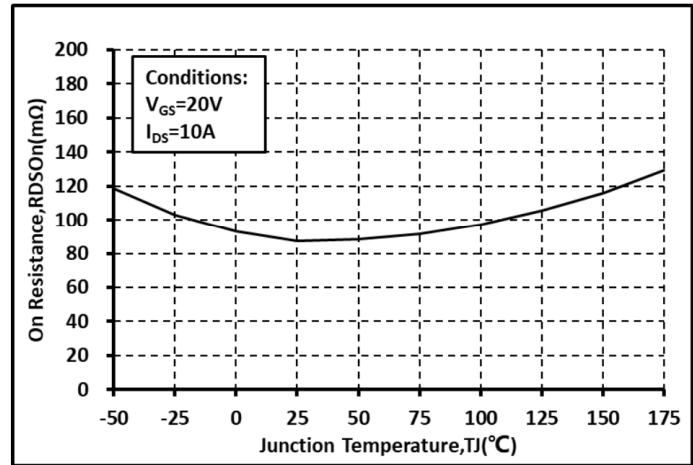


Fig. 4 Ron vs. Temperature

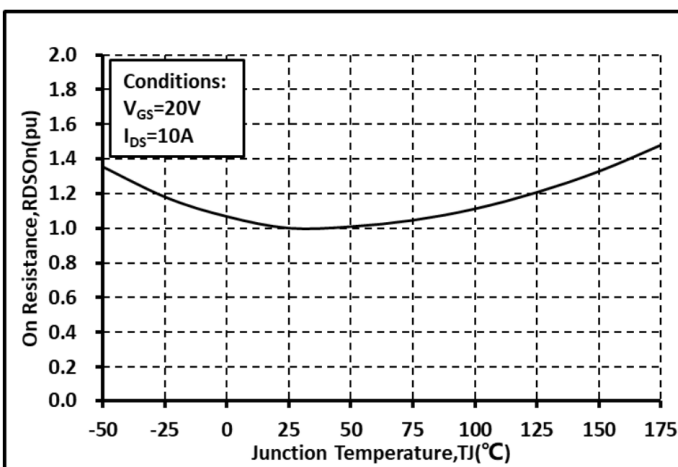


Fig. 5 Normalized Ron vs. Temperature

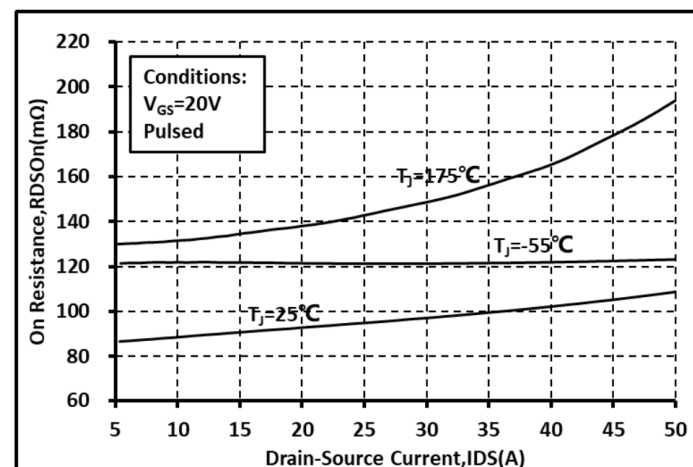


Fig. 6 Ron vs.  $I_{DS}$  @ Various Temperature

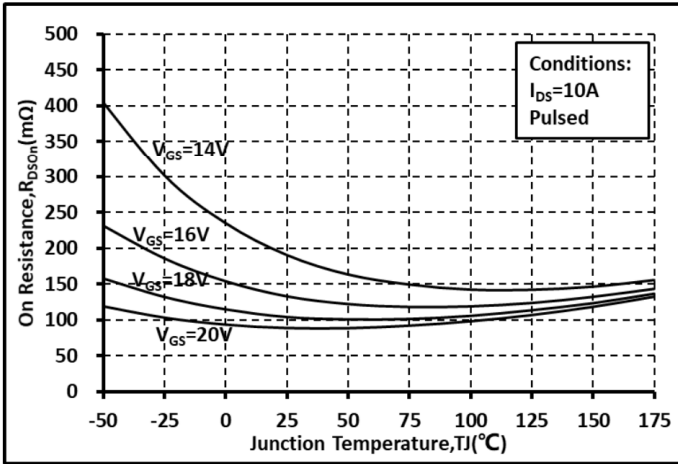


Fig. 7 Ron vs. Temperature @ Various  $V_{GS}$

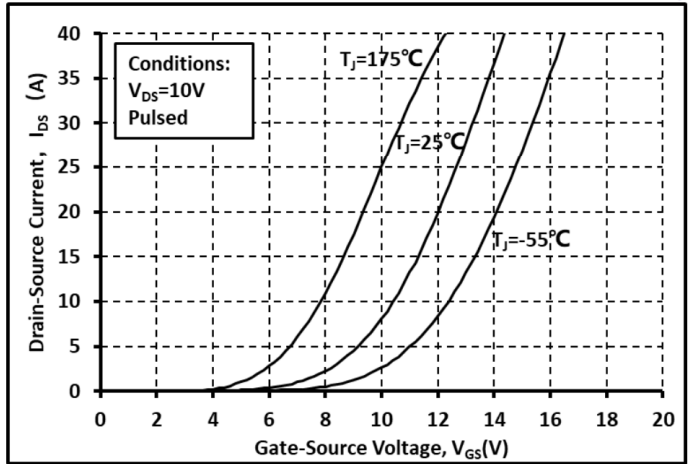


Fig. 8 Transfer Curves @ Various Temperature

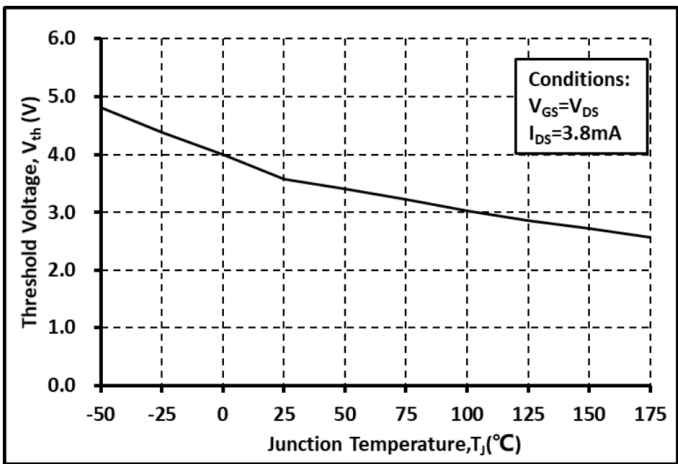


Fig. 9 Threshold Voltage vs. Temperature

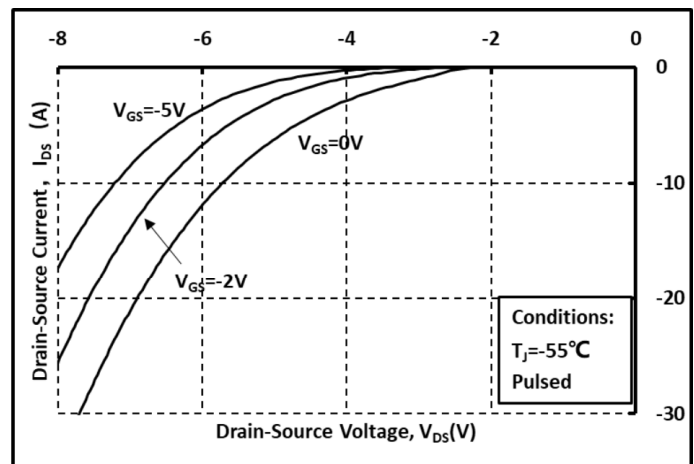


Fig. 10 Body Diode curves @  $T_J=-55^{\circ}C$

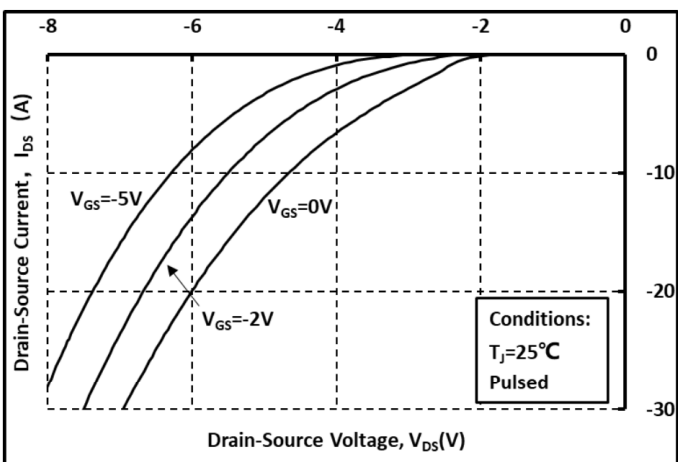


Fig. 11 Body Diode curves @  $T_J=25^{\circ}C$

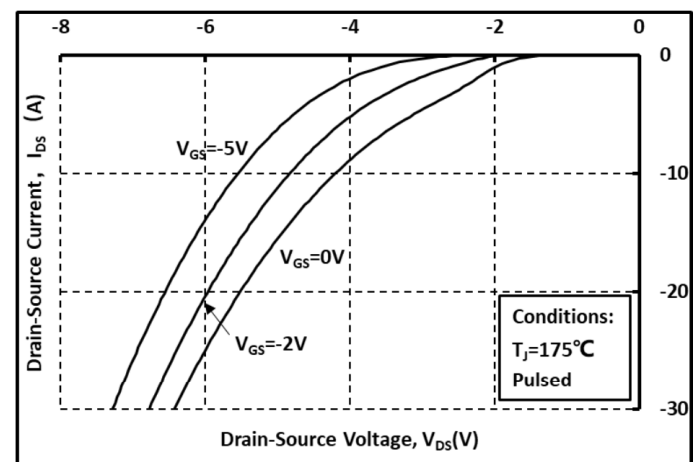


Fig. 12 Body Diode curves @  $T_J=175^{\circ}C$

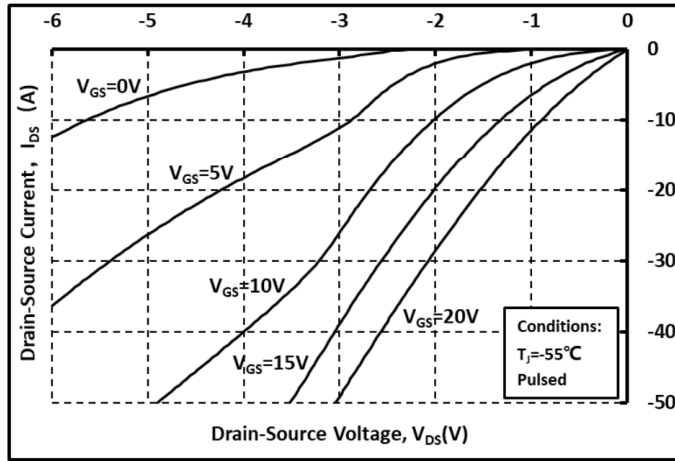


Fig. 13 3<sup>rd</sup> Quadrant curves @  $T_j = -55^\circ\text{C}$

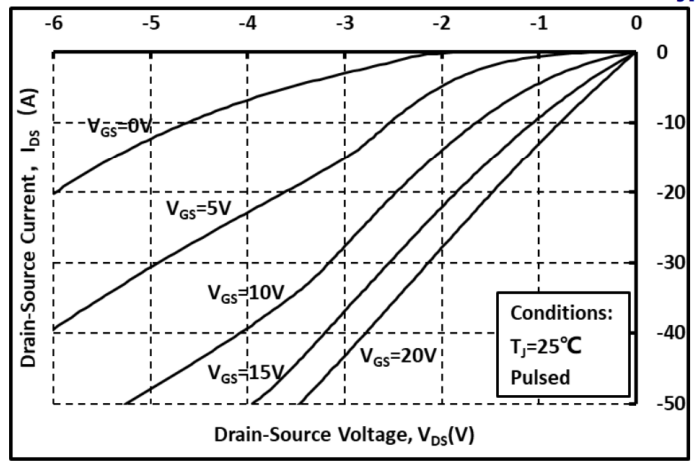


Fig. 14 3<sup>rd</sup> Quadrant curves @  $T_j = 25^\circ\text{C}$

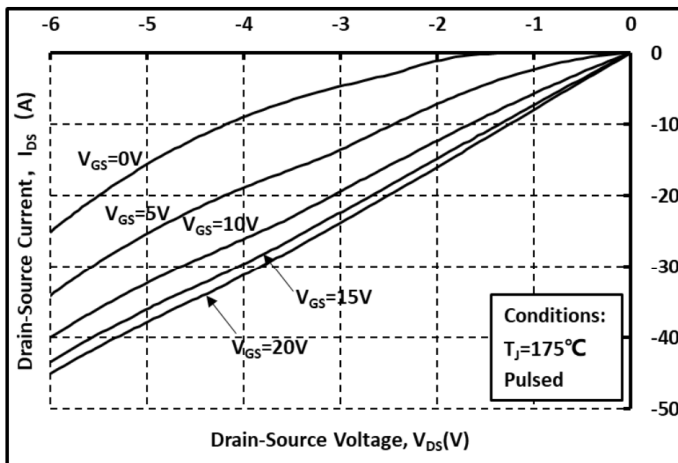


Fig. 15 3<sup>rd</sup> Quadrant curves @  $T_j = 175^\circ\text{C}$

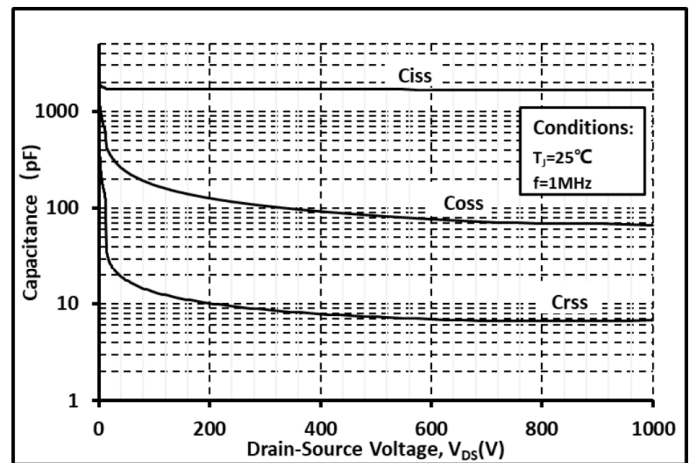


Fig. 16 Capacitance vs.  $V_{DS}$

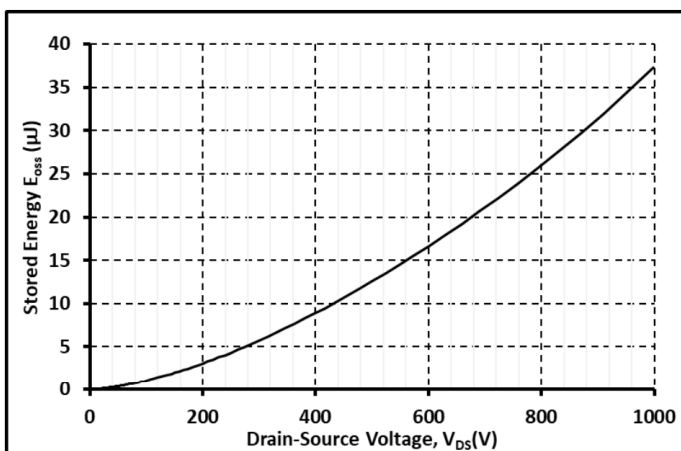


Fig. 17 Output Capacitor Stored Energy

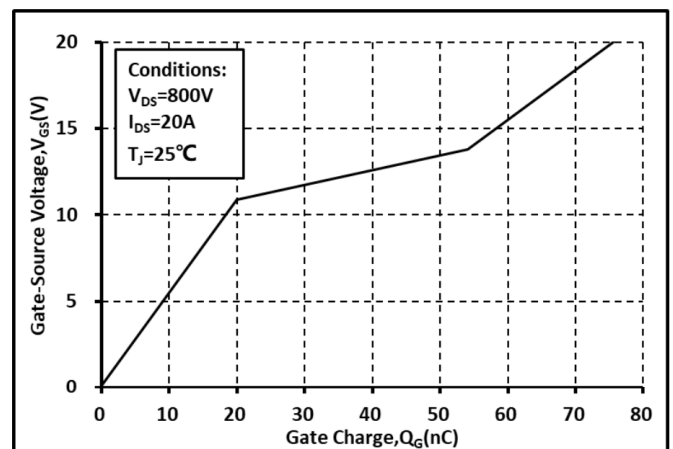


Fig. 18 Gate Charge Characteristics

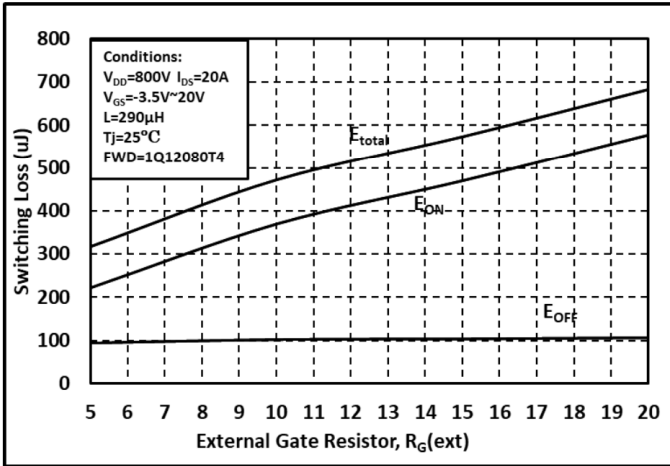


Fig. 19 Switching Energy vs.  $R_{G(ext)}$

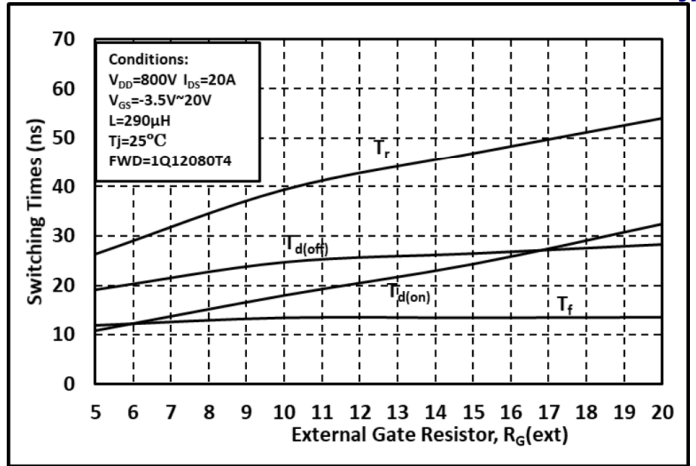


Fig. 20 Switching Times vs.  $R_{G(ext)}$

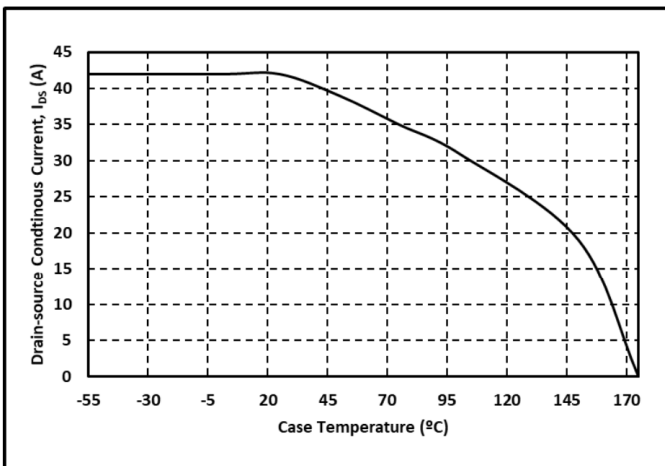


Fig. 21 Continuous Drain Current vs. Case Temperature

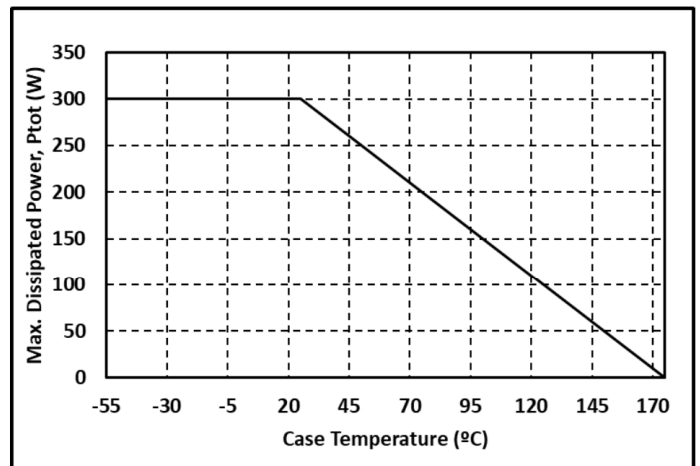


Fig. 22 Max. Power Dissipation Derating vs. Case Temperature

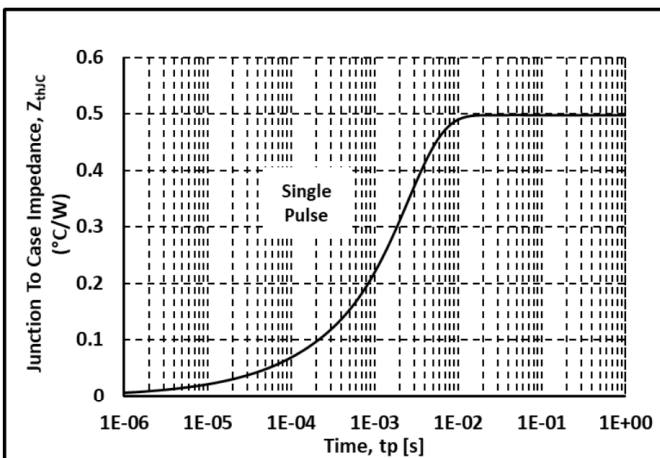


Fig. 23 Thermal impedance

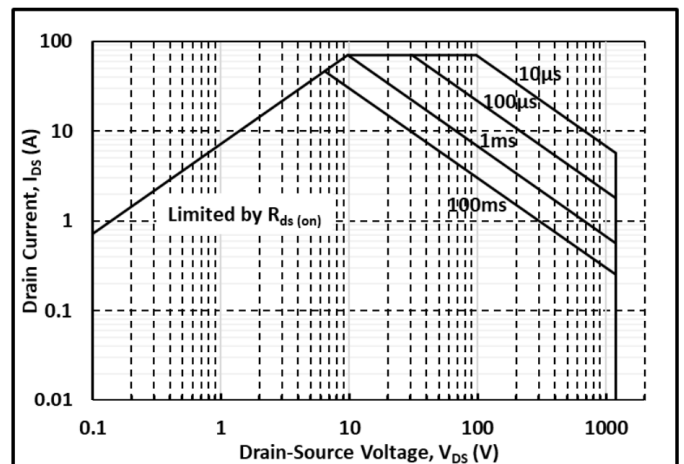
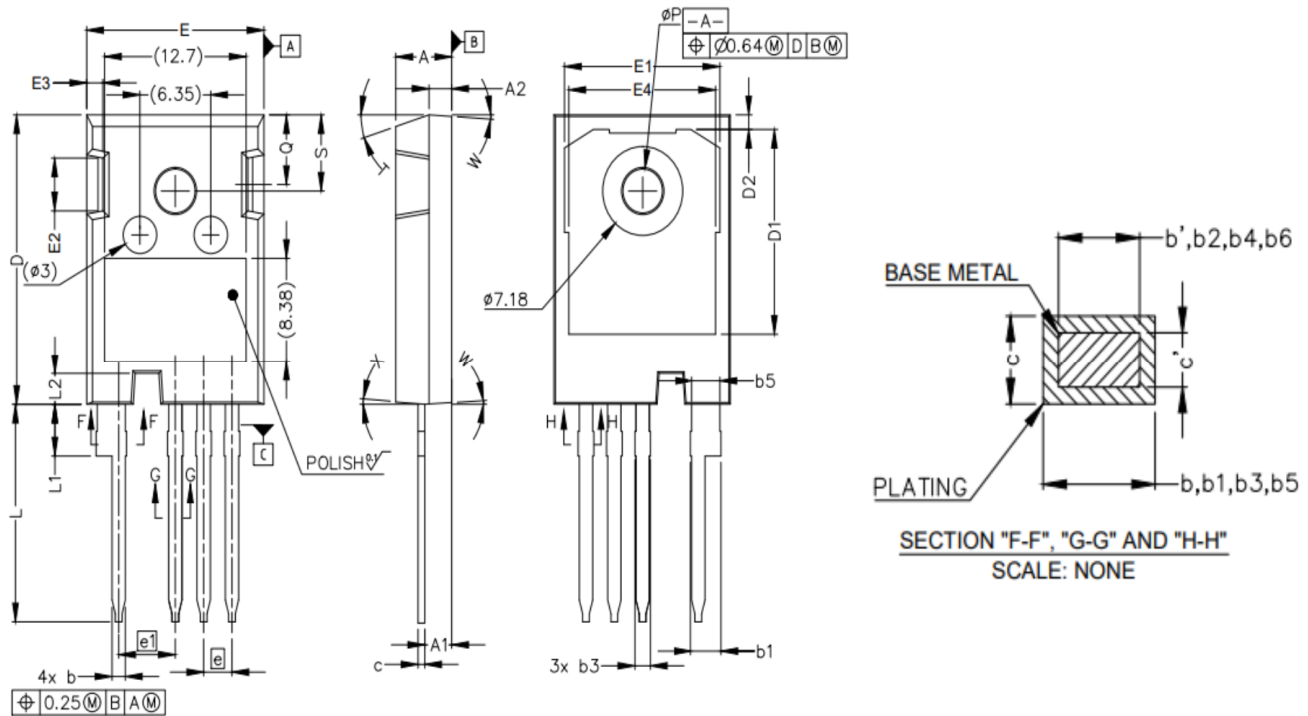


Fig. 24 Safe Operating Area

## TO-247\_4L PACKAGE OUTLINE



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.50	5.02	5.50	E1	12.50	14.02	15.00
A1	2.00	2.40	2.80	E2	3.00	4.40	5.00
A2	1.80	2.00	2.30	E3	0.80	1.45	2.10
b'	0.90	1.20	1.40	E4	11.50	13.26	14.00
b	0.90	1.20	1.45	e	2.54BSC		
b1	2.15	2.67	3.10	e1	5.08BSC		
b2	2.15	2.67	3.05	N	4.00		
b3	0.90	1.30	1.80	L	16.00	17.57	19.00
b4	0.90	1.30	1.70	L1	3.47	4.19	4.87
b5	2.20	2.53	2.89	L2	2.05	2.50	2.95
b6	2.20	2.53	2.84	$\phi P$	3.21	3.61	3.95
c'	0.48	0.60	0.75	Q	5.09	5.79	6.40
c	0.48	0.60	0.78	S	5.74	6.21	6.60
D	22.50	23.45	24.50	T	17.5°REF		
D1	15.50	16.55	18.10	W	3.5°REF		
D2	0.85	1.19	1.35	X	4°REF		
E	15.00	15.94	17.00				



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Din-Tek Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Din-Tek"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Din-Tek makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Din-Tek disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Din-Tek's knowledge of typical requirements that are often placed on Din-Tek products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Din-Tek's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Din-Tek products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Din-Tek product could result in personal injury or death. Customers using or selling Din-Tek products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Din-Tek personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Din-Tek. Product names and markings noted herein may be trademarks of their respective owners.

## Material Category Policy

**Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Din-Tek documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

**Din-Tek Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Din-Tek documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**